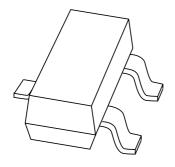
### DISCRETE SEMICONDUCTORS

# DATA SHEET



## BAL99 High-speed diode

Product data sheet Supersedes data of 1999 May 26 2003 Dec 12



### **High-speed diode**

**BAL99** 

#### **FEATURES**

- Small plastic SMD package
- High switching speed: max. 4 ns
- Continuous reverse voltage: max. 70 V
- Repetitive peak reverse voltage: max. 70 V
- Repetitive peak forward current: max. 500 mA.

### **APPLICATIONS**

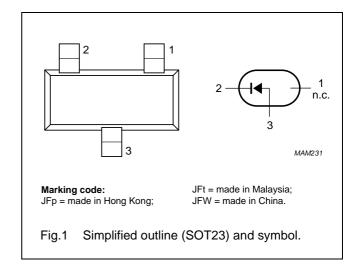
• High-speed switching in e.g. surface mounted circuits.

### **DESCRIPTION**

The BAL99 is a high-speed switching diode fabricated in planar technology, and encapsulated in the small SOT23 plastic SMD package.

#### **PINNING**

PIN	DESCRIPTION
1	not connected
2	cathode
3	anode



### **ORDERING INFORMATION**

TYPE NUMBER	PACKAGE					
TIPE NOWIBER	NAME	VERSION				
BAL99	_	plastic surface mounted package; 3 leads	SOT23			

### **LIMITING VALUES**

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
$V_{RRM}$	repetitive peak reverse voltage		_	70	V
V <sub>R</sub>	continuous reverse voltage		_	70	V
I <sub>F</sub>	continuous forward current	see Fig.2; note 1	_	215	mA
I <sub>FRM</sub>	repetitive peak forward current		_	500	mA
I <sub>FSM</sub>	non-repetitive peak forward current	square wave; $T_j = 25$ °C prior to surge; see Fig.4			
		t <sub>p</sub> = 1 μs	_	4	Α
		$t_p = 1 \text{ ms}$	_	1	Α
		t <sub>p</sub> = 1 s	_	0.5	Α
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> = 25 °C; note 1	_	250	mW
T <sub>stg</sub>	storage temperature		-65	+150	°C
T <sub>j</sub>	junction temperature		_	150	°C

#### Note

1. Device mounted on an FR4 printed-circuit board.

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### **ELECTRICAL CHARACTERISTICS**

 $T_j = 25$  °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MAX.	UNIT
V <sub>F</sub>	forward voltage	see Fig.3		
		I <sub>F</sub> = 1 mA	715	mV
		I <sub>F</sub> = 10 mA	855	mV
		I <sub>F</sub> = 50 mA	1	V
		I <sub>F</sub> = 150 mA	1.25	V
$I_R$	reverse current	see Fig.5		
		V <sub>R</sub> = 25 V	30	nA
		V <sub>R</sub> = 70 V	1	μΑ
		V <sub>R</sub> = 25 V; T <sub>j</sub> = 150 °C	30	μΑ
		$V_R = 70 \text{ V}; T_j = 150 \text{ °C};$	50	μΑ
$C_d$	diode capacitance	$f = 1 \text{ MHz}$ ; $V_R = 0$ ; see Fig.6	1.5	pF
t <sub>rr</sub>	reverse recovery time	when switched from $I_F = 10$ mA to $I_R = 10$ mA;	4	ns
		$R_L = 100 \Omega$ ; measured at $I_R = 1 \text{ mA}$ ; see Fig.7		
$V_{fr}$	forward recovery voltage	when switched from $I_F = 10 \text{ mA}$ ; $t_r = 20 \text{ ns}$ ; see Fig.8	1.75	V

### THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R <sub>th(j-tp)</sub>	thermal resistance from junction to tie-point		360	K/W
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	note 1	500	K/W

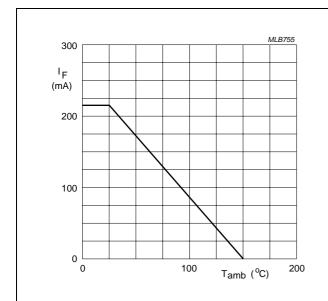
### Note

1. Device mounted on an FR4 printed-circuit board.

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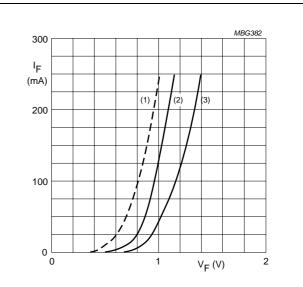
BAL99

### **GRAPHICAL DATA**



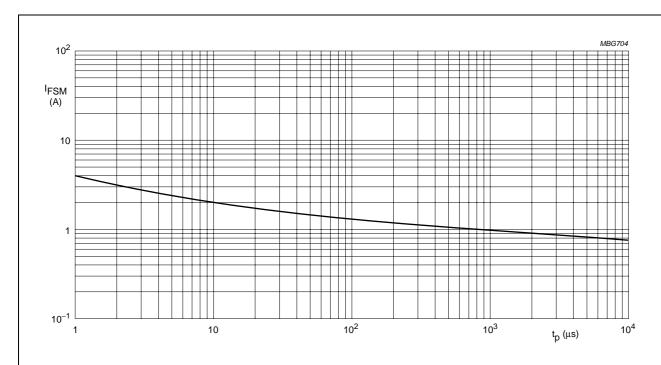
Device mounted on an FR4 printed-circuit board.

Fig.2 Maximum permissible continuous forward current as a function of ambient temperature.



- (1)  $T_i = 150 \,^{\circ}\text{C}$ ; typical values.
- (2)  $T_j = 25 \,^{\circ}\text{C}$ ; typical values.
- (3)  $T_j = 25$  °C; maximum values.

Fig.3 Forward current as a function of forward voltage.

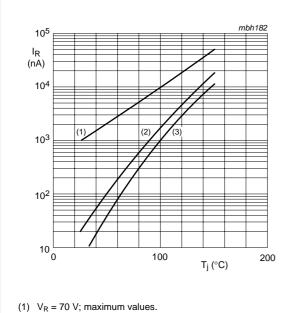


Based on square wave currents;  $T_j = 25$  °C prior to surge.

Fig.4 Maximum permissible non-repetitive peak forward current as a function of pulse duration.

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- (2)  $V_R = 70 \text{ V}$ ; typical values.
- (3)  $V_R = 25 \text{ V}$ ; typical values.

Fig.5 Reverse current as a function of junction temperature.

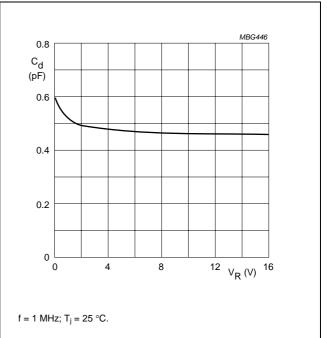


Fig.6 Diode capacitance as a function of reverse

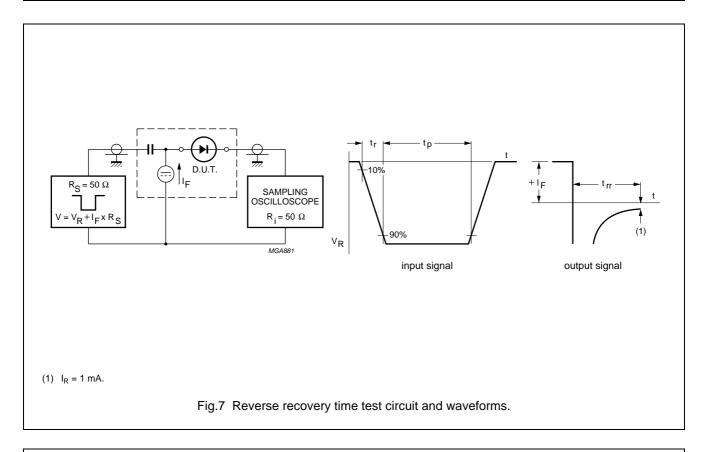
voltage; typical values.

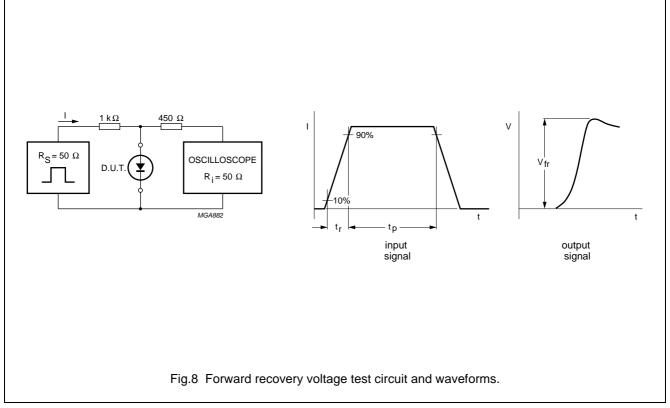
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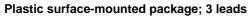




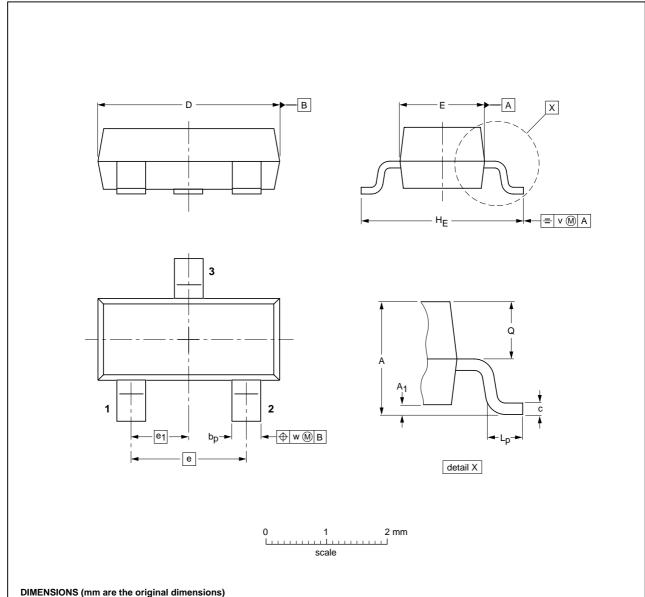
### High-speed diode

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### **PACKAGE OUTLINE**



SOT23



DIMENS	ЮИЗ (П	ım are tı	ne origir	iai dime	ensions)	
						=

UNIT	Α	A <sub>1</sub> max.	bp	С	D	E	е	e <sub>1</sub>	HE	Lp	Q	v	w
mm	1.1 0.9	0.1	0.48 0.38	0.15 0.09	3.0 2.8	1.4 1.2	1.9	0.95	2.5 2.1	0.45 0.15	0.55 0.45	0.2	0.1

OUTLINE		REFER	EUROPEAN	ISSUE DATE		
VERSION	IEC	EC JEDEC JEITA			PROJECTION	ISSUE DATE
SOT23		TO-236AB				<del>-04-11-04</del> 06-03-16

### High-speed diode

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#### **DATA SHEET STATUS**

DOCUMENT STATUS <sup>(1)</sup>	PRODUCT STATUS <sup>(2)</sup>	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

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### **Contact information**

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